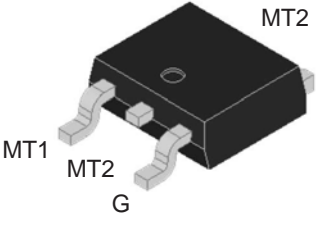
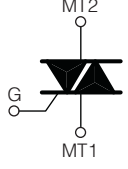


LOGIC LEVEL TRIAC

<p style="text-align: center;">DPAK (Plastic)</p>  	<p>On-State Current 8 Amp</p> <p>Gate Trigger Current < 10 mA</p>
	<p>Off-State Voltage 200 V ÷ 800V</p> <p>This series of TRIACs uses a high performance PNP technology.</p> <p>These parts are intended for general purpose AC switching applications with highly inductive loads.</p>

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Value	Unit
$I_{T(RMS)}$	RMS On-state Current (full sine wave)	All Conduction Angle, $T_c = 95\text{ }^\circ\text{C}$	8	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 60 Hz ($t = 16.7\text{ ms}$)	88	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 50 Hz ($t = 20\text{ ms}$)	80	A
I^2t	Fusing Current	$t_p = 10\text{ms}$, Half Cycle	32	A^2s
I_{GM}	Peak Gate Current	20 μs max. $T_j = 125\text{ }^\circ\text{C}$	4	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j = 125\text{ }^\circ\text{C}$	1	W
di/dt	Critical rate of rise of on-state current	$I_G = 2x I_{GT}$, $t_r \leq 100\text{ns}$ $f = 120\text{ Hz}$, $T_j = 125\text{ }^\circ\text{C}$	50	A/ μs
T_j	Operating Temperature		(-40 + 125)	$^\circ\text{C}$
T_{stg}	Storage Temperature		(-40 + 150)	$^\circ\text{C}$
T_{sld}	Soldering Temperature	10s max.	260	$^\circ\text{C}$

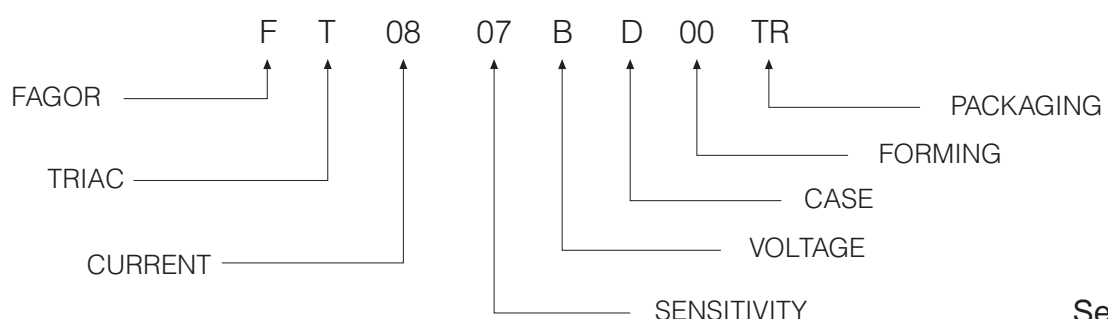
SYMBOL	PARAMETER	VOLTAGE					Unit
		B	D	M	S	N	
V_{DRM}	Repetitive Peak Off State	200	400	600	700	800	V
V_{RRM}	Voltage						

LOGIC LEVEL TRIAC
Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY		Unit
					07	08	
$I_{GT}^{(1)}$	Gate Trigger Current	$V_D = 12 V_{DC}, R_L = 33\Omega, T_j = 25^\circ C$	Q1÷Q3	MAX	5	10	mA
			Q4	MAX	7		mA
V_{GT}	Gate Trigger Voltage	$V_D = 12 V_{DC}, R_L = 33\Omega, T_j = 25^\circ C$	Q1÷Q3	MAX	1.3		V
			Q1÷Q4	MAX	1.3		V
V_{GD}	Gate Non Trigger Voltage	$V_D = V_{DRM}, R_L = 3.3 K\Omega, T_j = 125^\circ C$	Q1÷Q3	MIN	0.2		V
			Q1÷Q4	MIN	0.2		V
$I_H^{(2)}$	Holding Current	$I_T = 100 mA, \text{Gate open}, T_j = 25^\circ C$		MAX	15	15	mA
I_L	Latching Current	$I_G = 1.2 I_{GT}, T_j = 25^\circ C$	Q1,Q3	MAX		25	mA
			Q1,Q3,Q4	MAX	20		mA
			Q2	MAX	30	30	mA
$dV/dt^{(2)}$	Critical Rate of Voltage Rise	$V_D = 0.67 \times V_{DRM}, \text{Gate open}$ $T_j = 125^\circ C$		MIN	20	40	V/ μs
$(dI/dt)_c^{(2)}$	Critical Rate of Current Rise	$(dv/dt)_c = 0.1 V/\mu s, T_j = 125^\circ C$		MIN	3.5	5.4	A/ms
		$(dv/dt)_c = 10 V/\mu s, T_j = 125^\circ C$		MIN	1.5	2.8	A/ms
		without snubber $T_j = 125^\circ C$		MIN	-	-	
$V_{TM}^{(2)}$	On-state Voltage	$I_T = 5.5 \text{ Amp}, t_p = 380 \mu s, T_j = 25^\circ C$		MAX	1.6		V
$V_{t(o)}^{(2)}$	Threshold Voltage	$T_j = 125^\circ C$		MAX	0.85		V
$r_d^{(2)}$	Dynamic resistance	$T_j = 125^\circ C$		MAX	90		m Ω
I_{DRM}/I_{RRM}	Off-State Leakage Current	$V_D = V_{DRM}, T_j = 125^\circ C$		MAX	1		mA
		$V_R = V_{RRM}, T_j = 25^\circ C$		MAX	5		μA
$R_{th(j-c)}$	Thermal Resistance Junction-Case	for AC 360° conduction angle			1.8		°C/W
$R_{th(j-a)}$	Thermal Resistance Junction-Ambient	$S = 1cm^2$			70		°C/W

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION


LOGIC LEVEL TRIAC

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

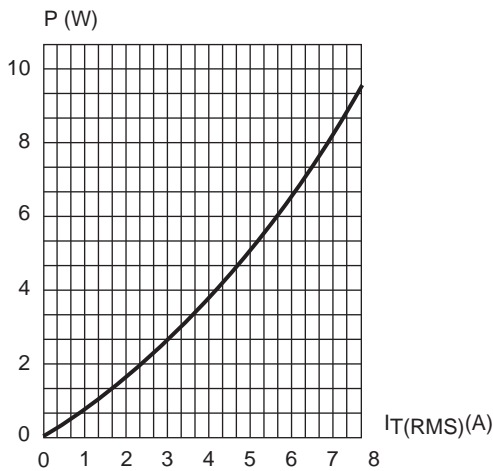


Fig. 2: RMS on-state current versus case temperature (full cycle).

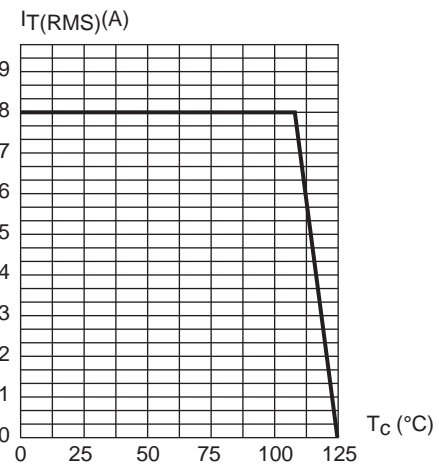


Fig. 3: Relative variation of thermal impedance versus pulse duration.

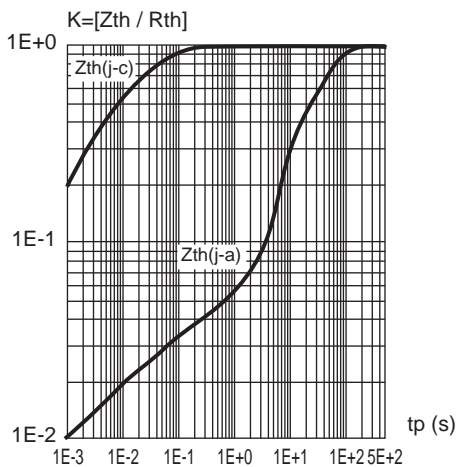


Fig. 4: On-state characteristics (maximum values)

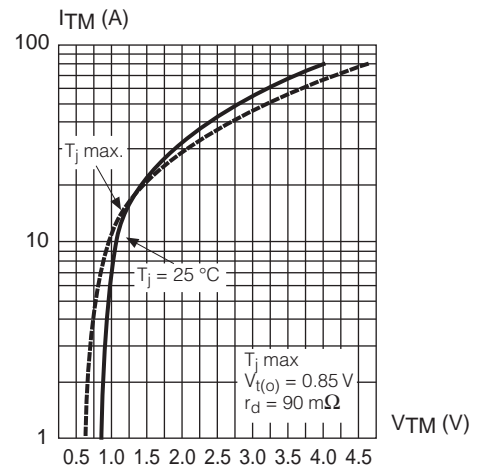


Fig. 5: Surge peak on-state current versus number of cycles

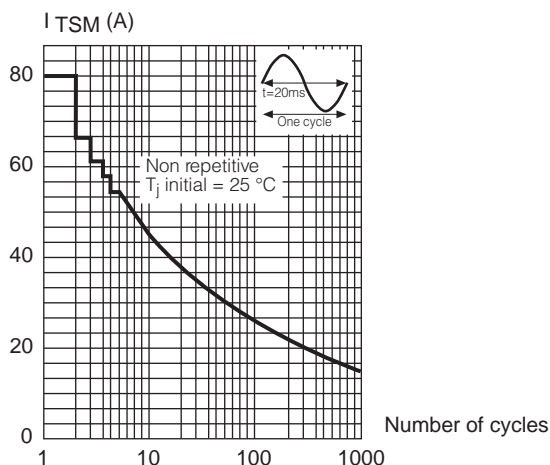
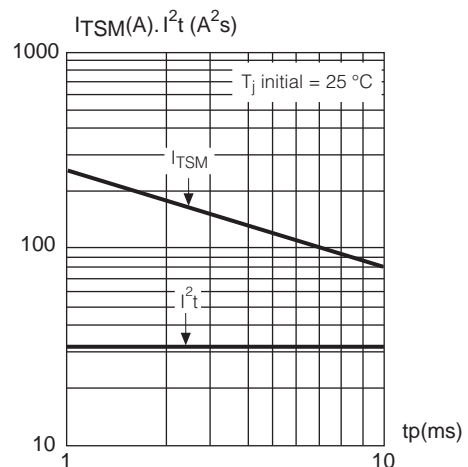


Fig. 6: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t_p < 10$ ms, and corresponding value of I^2t .



LOGIC LEVEL TRIAC

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

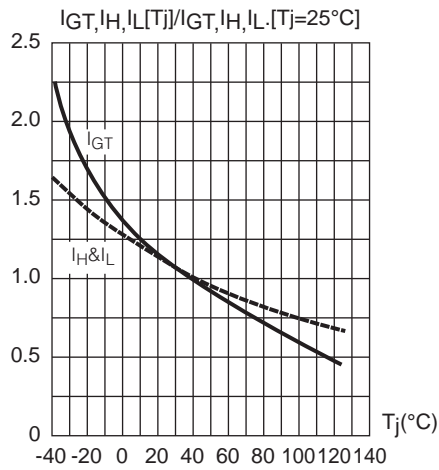


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature

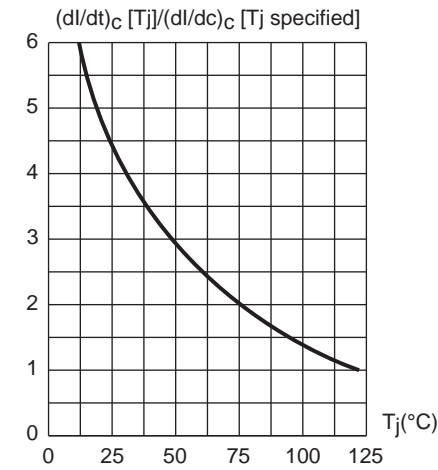
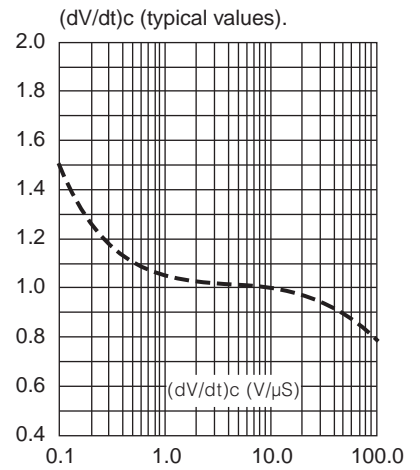


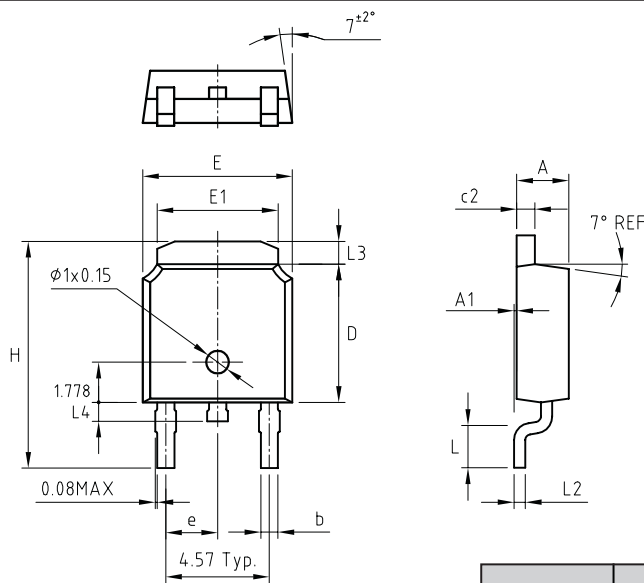
Fig. 9: Relative variation of critical rate of decrease of main current versus



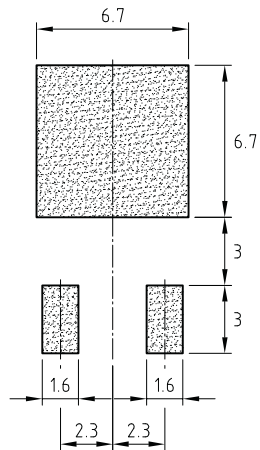
LOGIC LEVEL TRIAC

PACKAGE MECHANICAL DATA

DPAK / TO252-AA



FOOT PRINT (mm)



REF.	DIMENSIONS		
	Milimeters		
	Min.	Nominal	Max.
A	2.18	2.3	2.39
A1	0	0.127	0.127
b	0.64	0.75	0.89
c2	0.46	0.51	0.56
D	5.97	6.1	6.22
E	6.47	6.6	6.73
E1	5.20	5.34	5.46
e		2.28BSC	
H	9.77	10.03	10.28
L	1.31	1.44	1.57
L2	0.46	0.51	0.56
L3	0.89	1.02	1.14
L4	0.51	0.76	1.02

Marking: type number
Weight: 0.2 g